

Rong Zhang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

264
papers

3,650
citations

31
h-index

48
g-index

290
ext. papers

4,641
ext. citations

4.6
avg, IF

5.24
L-index

#	Paper	IF	Citations
264	Effect of current on the inhomogeneous light emission from AlGaInP-based flip-chip red mini-LEDs. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	3
263	Majority and Minority Carrier Traps in NiO/β-Ga ₂ O ₃ /p-n Heterojunction Diode. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	1
262	Enhancing deep-UV emission at 234 nm by introducing a truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets.. <i>Nanoscale</i> , 2022 , 14, 653-662	7.7	2
261	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 26-30 ²	7.2	3
260	70- μ m Body Ga ₂ O ₃ Schottky Barrier Diode with 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
259	Epitaxial Growth and Characteristics of Nonpolar a-Plane InGaIn Films with Blue-Green-Red Emission and Entire In Content Range. <i>Chinese Physics Letters</i> , 2022 , 39, 048101	1.8	0
258	M-Plane β-Ga ₂ O ₃ Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022 , 43, 541-544	4.4	2
257	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 1918-1923	2.9	
256	Demonstration of β-Ga ₂ O ₃ Superjunction-Equivalent MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 2203-2209	2.9	2
255	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic β-Ga ₂ O ₃ via Phase Engineering. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 461-468	4	2
254	Ga ₂ O ₃ /GaN Heterostructural Ultraviolet Photodetectors with Exciton-Dominated Ultranarrow Response. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 188-196	4	6
253	C-plane Blue Micro-LED with 1.53 GHz Bandwidth for High-speed Visible Light Communication. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	6
252	4H-SiC n-i-p extreme ultraviolet detector with gradient doping-induced surface junction. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	0
251	Field-Plated NiO/Ga ₂ O ₃ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 1-1	2.3	1
250	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1743-1746	4.4	0
249	Over 1200 V Normally-OFF p-NiO gated AlGaIn/GaN HEMTs on Si with a Small Threshold Voltage Shift. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	2
248	Optimization of annealing conditions for Ag/p-GaN ohmic contacts. <i>Applied Physics A: Materials Science and Processing</i> , 2021 , 127, 870	2.6	1

247	2.41 kV Vertical P-NiO/n-Ga ₂ O ₃ Heterojunction Diodes With a Record Baliga M ² Figure-of-Merit of 5.18 GW/cm ² . <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	12
246	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	1
245	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 nm thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 022202	1.3	1
244	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. <i>Crystals</i> , 2021 , 11, 403	2.3	4
243	Enhanced Stability and Sensitivity of AlGaIn/GaN-HEMTs pH Sensor by Reference Device. <i>IEEE Sensors Journal</i> , 2021 , 21, 9771-9776	4	2
242	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes 2021 ,		1
241	Demonstration of the p-NiOx/n-Ga ₂ O ₃ Heterojunction Gate FETs and Diodes With BV ₂ /Ron,sp Figures of Merit of 0.39 GW/cm ² and 1.38 GW/cm ² . <i>IEEE Electron Device Letters</i> , 2021 , 42, 485-488	4.4	28
240	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , 2021 , 10, 94	16.7	51
239	High-Reflectivity Mg/Al Ohmic Contacts on n-GaN. <i>IEEE Photonics Technology Letters</i> , 2021 , 33, 347-349	2.2	1
238	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability 2021 ,		4
237	Room-temperature intrinsic ferromagnetism in epitaxial CrTe ultrathin films. <i>Nature Communications</i> , 2021 , 12, 2492	17.4	42
236	Electrode-Dependent Electrical Properties of Detection-Band Tunable Ultraviolet Photodetectors Based on Ga ₂ O ₃ /GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2100166	1.6	0
235	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-8	1.8	1
234	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021 , 42, 974-977	4.4	13
233	3.4-kV AlGaIn/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. <i>IEEE Electron Device Letters</i> , 2021 , 42, 208-211	4.4	8
232	High-performance normally off p-GaN gate high-electron-mobility transistor with In _{0.17} Al _{0.83} N barrier layer design. <i>Optical and Quantum Electronics</i> , 2021 , 53, 1	2.4	3
231	Impurity band assisted carrier relaxation in Cr doped topological insulator Bi ₂ Se ₃ . <i>Applied Physics Letters</i> , 2021 , 118, 081103	3.4	2
230	46.4: Fabrication of InGaIn/GaN-based nano-LEDs for display applications. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 568-568	0.5	

229	Tuning interfacial spin pump in Ta/CoFeB/MgO films by ultrafast laser pulse. <i>Applied Physics Letters</i> , 2021 , 119, 092404	3.4	0
228	Giant Topological Hall Effect in van der Waals Heterostructures of CrTe/BiTe. <i>ACS Nano</i> , 2021 , 15, 15710-15719	16.7	5
227	Growth and nitridation of EGa_2O_3 thin films by Sol-Gel spin-coating epitaxy with post-annealing process. <i>Journal of Sol-Gel Science and Technology</i> , 2021 , 100, 183-191	2.3	3
226	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. <i>Nature Nanotechnology</i> , 2021 , 16, 1231-1236	28.7	20
225	VT Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1508-1511	4.4	8
224	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12163-12167	7.2	6
223	1.37 kV/12 A NiO/ EGa_2O_3 Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12213-12217	7.2	19
222	1.95-kV Beveled-Mesa NiO/ EGa_2O_3 Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	13
221	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\text{EGa}_2\text{O}_3/\text{In}_2\text{O}_3$ Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 795-803	4	2
220	Manipulation of Gilbert damping in ultrathin half-metallic $\text{Co}_2\text{FeAl}_{1-x}$ by composition-deficiency-compensation. <i>Applied Physics Letters</i> , 2020 , 116, 212406	3.4	4
219	Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 425101	3	2
218	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 2070028	1.6	
217	EGa_2O_3 Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 1-1	4.4	4
216	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 791-794	2.2	4
215	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 706-709	2.2	1
214	Polarization-Independent Indium Phosphide Nanowire Photodetectors. <i>Advanced Optical Materials</i> , 2020 , 8, 2000514	8.1	3
213	Realization of regular resonance mode in GaN-based polygonal microdisks on Si. <i>Journal of Applied Physics</i> , 2020 , 127, 113102	2.5	0
212	Band Alignment and Interface Recombination in NiO/ EGa_2O_3 Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3341-3347	2.9	24

211	High-Responsivity Graphene/4H-SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. <i>Advanced Optical Materials</i> , 2020 , 8, 2000559	8.1	8
210	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 808-816	4	6
209	Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , 2020 , 116, 062104	3.4	19
208	Investigation of the Electroluminescence Mechanism of GaN-Based Blue and Green Light-Emitting Diodes with Junction Temperature Range of 120B73 K. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 444	2.6	7
207	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020 , 41, 469-472	4.4	7
206	Mg acceptor activation mechanism and hole transport characteristics in highly Mg-doped AlGaIn alloys. <i>Chinese Physics B</i> , 2020 , 29, 058103	1.2	2
205	1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse p-n Junction Termination. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 1-1	2.3	6
204	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020 , 32, e1904354	24	11
203	Light-Tunable Ferromagnetism in Atomically Thin Fe ₃ GeTe ₂ Driven by Femtosecond Laser Pulse. <i>Physical Review Letters</i> , 2020 , 125, 267205	7.4	17
202	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline EGa ₂ O ₃ nanowire arrays. <i>Nanophotonics</i> , 2020 , 9, 4497-4503	6.3	9
201	Element-specific spin and orbital moments and perpendicular magnetic anisotropy in Ta/CoFeB/MgO structures. <i>Journal of Applied Physics</i> , 2020 , 127, 063903	2.5	3
200	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020 , 128, 235704	2.5	1
199	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900729	1.6	3
198	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900763	1.6	
197	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020 , 52, 1	2.4	0
196	Charge transfer dynamics of the CdTe quantum dots fluorescence quenching induced by ferrous (II) ions. <i>Applied Physics Letters</i> , 2020 , 116, 012105	3.4	6
195	High- β HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 15-19	2.3	7
194	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020 , 16, e1906205	11	9

193	Direct observation of ferrimagnetic ordering in inverse Heusler alloy Mn ₂ CoAl. <i>Applied Physics Letters</i> , 2020 , 117, 012401	3.4	2
192	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1-diybis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 2070029	1.6	
191	Bi ₂ O ₂ Se/Au-Based Schottky Phototransistor With Fast Response and Ultrahigh Responsivity. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1464-1467	4.4	2
190	Strong interface-induced spin-charge conversion in YIG/Cr heterostructures. <i>Applied Physics Letters</i> , 2020 , 117, 112402	3.4	6
189	Different I-V Behaviors and Leakage Current Mechanisms in AlGa _N Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2716-2720	4	1
188	Optical Performance of Top-Down Fabricated AlGa _N Nanorod Arrays with Multi-Quantum Wells Embedded. <i>Nanoscale Research Letters</i> , 2019 , 14, 170	5	1
187	Tailoring exciton dynamics of monolayer transition metal dichalcogenides by interfacial electron-phonon coupling. <i>Communications Physics</i> , 2019 , 2,	5.4	19
186	Ultrafast Orbital-Oriented Control of Magnetization in Half-Metallic La Sr MnO Films. <i>Advanced Materials</i> , 2019 , 31, e1806443	24	11
185	Gate Reliability of p-GaN Gate AlGa _N /Ga _N High Electron Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 379-382	4.4	16
184	Observation of Small Polaron and Acoustic Phonon Coupling in Ultrathin La _{0.7} Sr _{0.3} MnO ₃ /SrTiO ₃ Structures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1800657	2.5	2
183	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on InGaO Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 7131-7137	9.5	38
182	Performance Modulation for Back-Illuminated AlGa _N Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-7	1.8	4
181	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. <i>Scientific Reports</i> , 2019 , 9, 8796	4.9	18
180	On-chip engineering of high-dimensional path-entangled states in a quadratic coupled-waveguide system. <i>Physical Review A</i> , 2019 , 99,	2.6	3
179	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 20956-20964	9.5	22
178	Ultrafast free carrier dynamics in black phosphorus-molybdenum disulfide (BP/MoS ₂) heterostructures. <i>Nanoscale Horizons</i> , 2019 , 4, 1099-1105	10.8	26
177	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGa _N /Ga _N HEMTs for High-Frequency Application. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1	2.3	0
176	Experimental observation of dual magnetic states in topological insulators. <i>Science Advances</i> , 2019 , 5, eaav2088	14.3	15

175	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 447-450	2.2	6
174	Evidence of anisotropic Landau level splitting in topological semimetal ZrSiS under high magnetic fields. <i>Frontiers of Physics</i> , 2019 , 14, 1	3.7	
173	Electrolyte gate controlled metal-insulator transitions of the CaZrO ₃ /SrTiO ₃ heterointerface. <i>Applied Physics Letters</i> , 2019 , 115, 061601	3.4	9
172	A High-Performance SiO ₂ /SiN _x 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-7	1.8	2
171	Precise Extraction of Dynamic R _{dson} Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1	2.3	5
170	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional Bi ₂ O ₂ Se Nanosheets. <i>Advanced Functional Materials</i> , 2019 , 29, 1905806	15.6	53
169	Single-crystal GaN layer converted from EGa ₂ O ₃ films and its application for free-standing GaN. <i>CrystEngComm</i> , 2019 , 21, 1224-1230	3.3	8
168	Janus Ga ₂ SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019 , 3, 1900321	7.1	5
167	Strain-driven lattice distortion and the resultant magnetic properties of La _{0.7} Sr _{0.3} MnO ₃ /BaTiO ₃ superlattices. <i>Applied Physics Letters</i> , 2019 , 115, 201604	3.4	3
166	All-carbon hybrids for high-performance electronics, optoelectronics and energy storage. <i>Science China Information Sciences</i> , 2019 , 62, 1	3.4	4
165	23.3: Invited Paper: Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 225-227	0.5	
164	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1929-1932	4.4	6
163	Observation and Modeling of Leakage Current in AlGa _N Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 1697-1700	2.2	2
162	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2019 , 32, e2482	1	3
161	Carbonized Bamboos as Excellent 3D Solar Vapor-Generation Devices. <i>Advanced Materials Technologies</i> , 2019 , 4, 1800593	6.8	68
160	Topological Phase Transition-Induced Triaxial Vector Magnetoresistance in (BiIn)Se Nanodevices. <i>ACS Nano</i> , 2018 , 12, 1537-1543	16.7	11
159	Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO ₃ Epitaxial Thin Film System. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800055	6.4	19
158	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 805-808	2.2	6

157	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. <i>IEEE Electron Device Letters</i> , 2018 , 39, 599-602	4.4	27
156	Transport evidence of 3D topological nodal-line semimetal phase in ZrSiS. <i>Frontiers of Physics</i> , 2018 , 13, 1	3.7	22
155	Identification and modulation of electronic band structures of single-phase Γ (Al _x Ga _{1-x}) ₂ O ₃ alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , 2018 , 113, 041901	3.4	29
154	The Effect of the Original Thickness of Ag in the Graphene/Ag Nanodots Transparent Conductive Layer on the Electrical and Optical Properties of GaN-Based UV-LEDs. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3803-3808	2.9	2
153	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018 , 18,	3.8	11
152	Ultrahigh Hall mobility and suppressed backward scattering in layered semiconductor Bi ₂ O ₂ Se. <i>Applied Physics Letters</i> , 2018 , 113, 072106	3.4	21
151	Observation of bimolecular recombination in high mobility semiconductor Bi ₂ O ₂ Se using ultrafast spectroscopy. <i>Applied Physics Letters</i> , 2018 , 113, 061104	3.4	7
150	Photoresponsivity of an all-semimetal heterostructure based on graphene and WTe. <i>Scientific Reports</i> , 2018 , 8, 12840	4.9	10
149	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. <i>ACS Nano</i> , 2018 , 12, 7327-7334	16.7	7
148	Emergent Ferromagnetism: Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO ₃ Epitaxial Thin Film System (Adv. Electron. Mater. 6/2018). <i>Advanced Electronic Materials</i> , 2018 , 4, 1870030	6.4	
147	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2018 , 31, e2299	1	1
146	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700368	1.6	4
145	Layered Topological Insulators and Semimetals for MagnetoResistance Type Sensors. <i>Advanced Quantum Technologies</i> , 2018 , 2, 1800039	4.3	6
144	First-principles insights on the electronic and optical properties of ZnO@CNT core@shell nanostructure. <i>Scientific Reports</i> , 2018 , 8, 15464	4.9	10
143	Highly efficient solar steam generation by hybrid plasmonic structured TiN/mesoporous anodized alumina membrane. <i>Journal of Materials Research</i> , 2018 , 33, 3857-3869	2.5	13
142	Enhanced p-type conduction in AlGaIn grown by metal-source flow-rate modulation epitaxy. <i>Applied Physics Letters</i> , 2018 , 113, 072107	3.4	16
141	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018 , 18, 3414-3420	11.5	25
140	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800069	1.6	6

139	A robust and tuneable mid-infrared optical switch enabled by bulk Dirac fermions. <i>Nature Communications</i> , 2017 , 8, 14111	17.4	126
138	Unsaturated magnetoconductance of epitaxial La _{0.7} Sr _{0.3} MnO ₃ thin films in pulsed magnetic fields up to 60 T. <i>AIP Advances</i> , 2017 , 7, 056404	1.5	7
137	Nontrivial surface state transport in Bi ₂ Se ₃ topological insulator nanoribbons. <i>Applied Physics Letters</i> , 2017 , 110, 053108	3.4	10
136	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGaN Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	4
135	Current transport mechanisms in Pt/Au Schottky contacts to AlInGaN using AlGaN/InGaN short-period superlattices. <i>Applied Physics A: Materials Science and Processing</i> , 2017 , 123, 1	2.6	1
134	Controllable synthesis and magnetotransport properties of Cd ₃ As ₂ Dirac semimetal nanostructures. <i>RSC Advances</i> , 2017 , 7, 17689-17696	3.7	18
133	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8	1.8	7
132	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. <i>Scientific Reports</i> , 2017 , 7, 44399	4.9	6
131	Graphene-carbon nanotube hybrid films for high-performance flexible photodetectors. <i>Nano Research</i> , 2017 , 10, 1880-1887	10	44
130	Giant Tunability of the Two-Dimensional Electron Gas at the Interface of BaO/SrTiO ₃ . <i>Nano Letters</i> , 2017 , 17, 6878-6885	11.5	29
129	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase InGaO/ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 36997-37005	9.5	106
128	Study of LED Thermal Resistance and TIM Evaluation Using LEDs With Built-in Sensor. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1856-1859	2.2	1
127	Broadband hot-carrier dynamics in three-dimensional Dirac semimetal Cd ₃ As ₂ . <i>Applied Physics Letters</i> , 2017 , 111, 091101	3.4	32
126	Bandgap renormalization in single-wall carbon nanotubes. <i>Scientific Reports</i> , 2017 , 7, 11221	4.9	9
125	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , 2017 , 7, 7503	4.9	10
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